

ABSTRACT OF THE DISCLOSURE

A solid state image device capable of improving charge transfer efficiency by reducing the interval between adjacent gate electrodes and reducing power consumption by reducing parasitic capacitances while obtaining a signal having small noise is provided. This solid state image device comprises a first gate electrode, formed on a gate insulator film, having a substantially flat upper surface and a second gate electrode formed on the gate insulator film through an insulator film having a thickness smaller than the minimum limit dimension of lithography to be adjacent to the first gate electrode without overlapping the first gate electrode.